Abstract

A semiconductor device has a dielectric film made of a fluorine-added carbon film formed on a substrate, a metallic layer formed on the fluorine-added carbon film and an adhesive layer formed between the dielectric film and the metallic layer. The adhesive layer is made of a compound layer having carbon and the metal (or metal the same as the metal included in the metallic layer), to protect the metallic layer from being peeled-off from the fluorine-added carbon film.